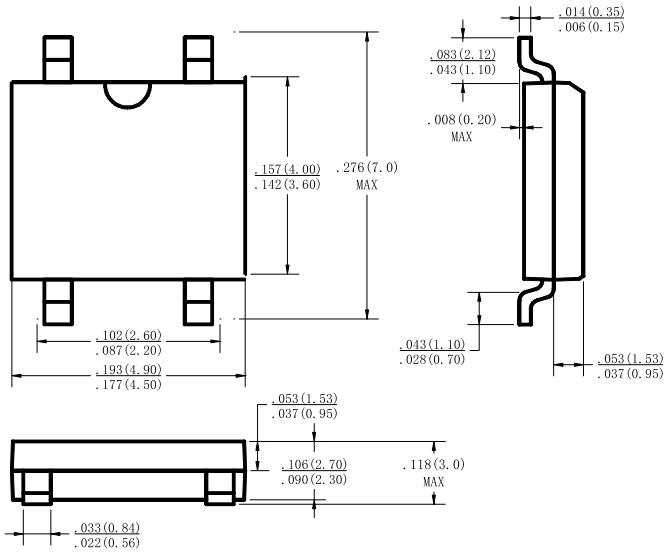
东沃电子
DOWOSEMI

MB1S THRU MB10S

■外形尺寸和印记 Outline Dimensions and Mark

MBS



Dimensions in inches and (millimeters)

■特征 Features

- I_o 0.8A
- V_{RRM} 100V~1000V
- 玻璃钝化芯片
  Glass passivated chip
- 耐正向浪涌电流能力高
  High surge forward current capability

■用途 Applications

- 作一般电源单相桥式整流用
  General purpose 1 phase Bridge rectifier applications

■极限值（绝对最大额定值）
Limiting Values（Absolute Maximum Rating）

参数名称 Item	符号 Symbol	单位 Unit	条件 Conditions		MB 1S	2S	4S	6S	8S	10S
反向重复峰值电压 Repetitive Peak Reverse Voltage	V_{RRM}	V			100	200	400	600	800	1000
平均整流输出电流 Average Rectified Output Current	I_O	A	60Hz正弦波，电阻负载，Ta 25℃ 60Hz sine wave, R-load, Ta=2 ℃	安装在氧化铝基板上 On alumina substrate	0.8					
				安装在玻璃-环氧基板上 On glass-epoxi substrate	0.5					
正向（不重复）浪涌电流 Surge(Non repetitive)Forward Current	I_{FSM}	A	60Hz正弦波，一个周期，T_j=2 ℃ 60Hz sine wave, 1 c cle, T_j=2 ℃		30					
正向浪涌电流的平方对电流浪涌持续时间的积分值 Current Squared Time	I^2t	A^2S	1ms≤t<8.3ms Tj 25℃，单个二极管 1ms≤t<8.3ms Tj=25 ，Rating of per diode		3.7					
存储温度 Storage Temperature	T_{stg}				-55 ~+150					
结温 Junction Temperature	T_j				-55 ~+150					

■电特性 （Ta=25℃ 除非另有规定）
Electrical Characteristics (T_a=25℃ Unless otherwise specified）

参数名称 Item	符号 Symbol	单位 Unit	测试条件 Test Condition	最大值 Max
正向峰值电压 Peak Forward Voltage	V_{FM}	V	I_{FM}=0.4A, 脉冲测试，单个二极管的额定值 I_{FM}=0.4A, Pulse measurement, Rating of per diode	1.05
反向峰值电流 Peak Reverse Current	I_{RRM}	μA	V_{RM}=V_{RRM} ,脉冲测试，单个二极管的额定值 V_{RM}=V_{RRM} , Pulse measurement, Rating of per diode	10
热阻 Thermal Resistance	$R_{\theta J-A}$	℃/W	结和环境之间，安装在氧化铝基板上 Between junction and ambient, On alumina substrate	76
			结和环境之间，安装在玻璃-环氧基板上 Between junction and ambient, On glass-epoxi substrate	134
	$R_{\theta J-L}$		结和引线之间 Between junction and lead	20

■特性曲线（典型）

图1：Io-Ta曲线
FIG1:Io-Ta Curve

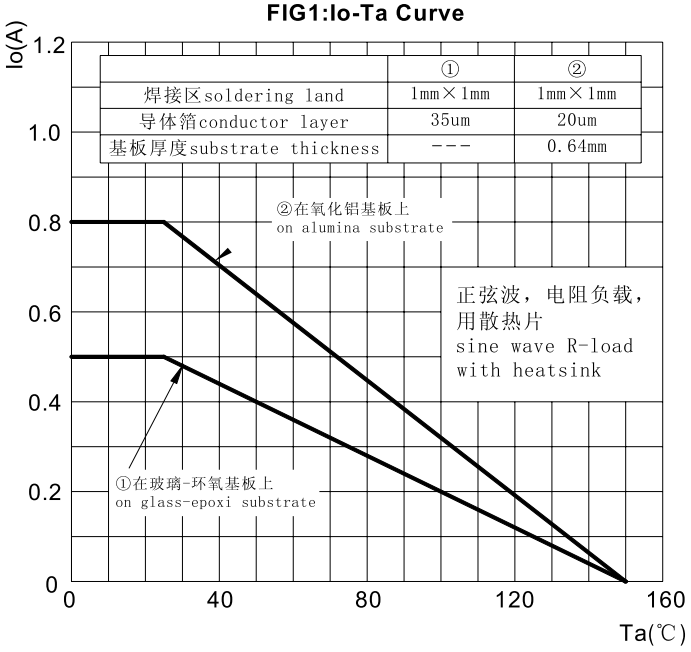


图2：耐正向浪涌电流曲线
FIG2:Surge Forward Current Capadility

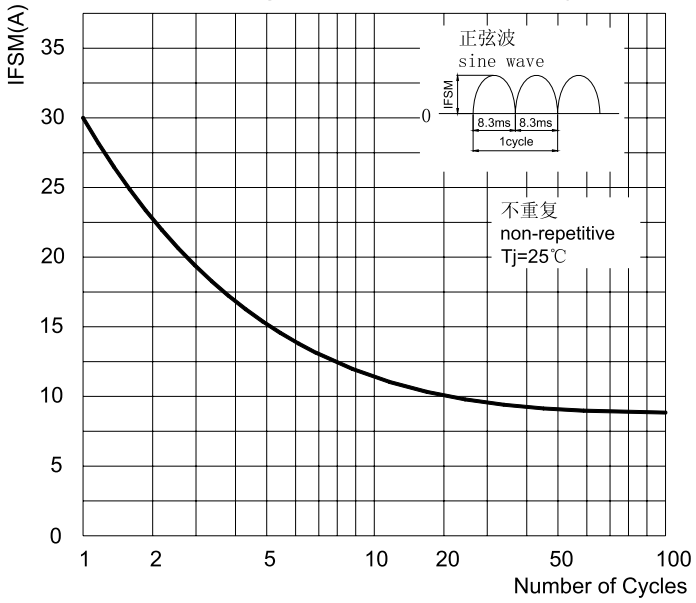


图3：正向电压曲线
FIG3: Forward Voltage

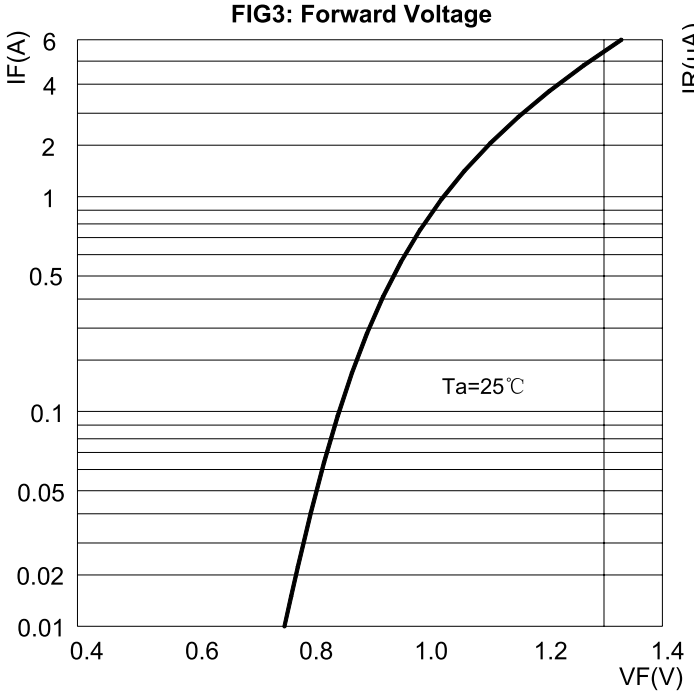


图4：反向电流曲线
FIG4:Typical Reverse Characteristics